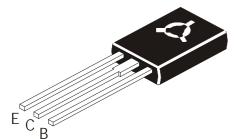


# NPN SILICON EPITAXIAL TRANSISTOR

2N4923 TO-126



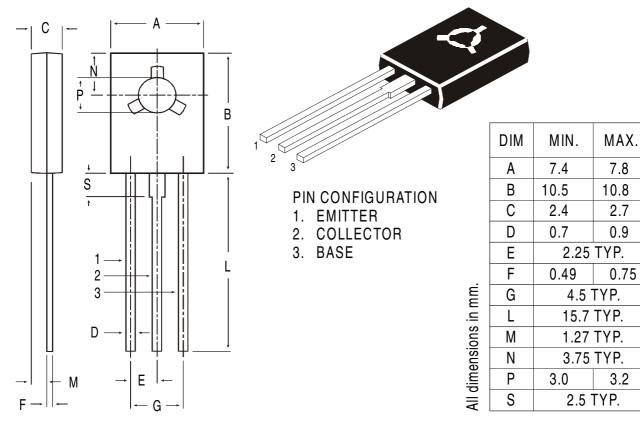
# **General Purpose Power Transistor**

#### ABSOLUTE MAXIMUM RATINGS (Ta=25 deg C) DESCRIPTION VALUE UNIT **Collector -Base Voltage** VCBO 80 V **Collector -Emitter Voltage** V VCEO 80 **Emitter Base Voltage** VEBO 5.0 V **Collector Current Continuous** 3.0 А IC **Base Current** IB 1.0 А Power Dissipation @ Tc=25 deg C PD W 30 Derate Above 25 deg C 0.24 W/deg C **Operating And Storage Junction** -65 to +150 deg C Tj, Tstg Temperature Range Lead Temperature for Soldering 1/16" TL 260 deg C from Body for 10 Seconds. **Thermal Resistance Junction to Case** 4.16 deg C/W Rth (j-c)

### ELECTRICAL CHARACTERISTICS (Ta=25 deg C Unless Otherwise Specified)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Collector -Emitter Sustaining Voltage	VCEO(sus)	IC=100mA, IB=0	80	-	-	V
Collector Cut off Current	ICEO	VCE=40V, IB=0	-	-	0.5	mA
	ICBO	VCB=80V, IE=0	-	-	0.1	mA
	ICEX	VCB=80V,VEB(0ff)=1.5V	-	-	0.1	mA
		Tc=125 deg C				
		VCB=80V,VEB(0ff)=1.5V	-	-	0.5	mA
Emitter Cut off Current	IEBO	VEB=5V, IC=0	-	-	1.0	mA
DC Current Gain	hFE *	IC=50mA,VCE=1V	40	-	-	-
		IC=500mA,VCE=1V	30		150	
		IC=1A,VCE=1V	10		-	-
Collector Emitter Saturation Voltage	VCE(sat)*	IC=1A, IB=0.1A	-		0.6	V
Base Emitter Saturation Voltage	VBE(sat)*	IC=1A, IB=0.1A	-		1.3	V
Base Emitter on Voltage	VBE(on) *	IC=1A,VCE=1V	-		1.3	V
DYNAMIC CHARACTERISTICS						
Transistors frequency	ft	IC=250mA,VCE=10V,f=1MHz	3.0	-	-	MHz
Output Capacitance	Cob	VCB=10V, IE=0, f=100kHz	-	-	100	pF
Small Signal Current Gain	hfe	IC=250mA,VCE=10V,f=1kHz	25	-	-	
*Pulse Test PW=300us, Duty Cycle=2%						

# TO-126 (SOT-32) Plastic Package



# Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX			
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt	
T0-126	500 pcs/polybag	340 gm/500 pcs	3" x 7.5" x 7.5"	2.0K	17" x 15" x 13.5"	32.0K	31 kgs	

# Disclaimer

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Data Sheet